



**THE DATASHEET OF  
DMN10H220L-13**



## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>A</sub> = +25°C
100V	220mΩ @ V <sub>GS</sub> = 10V	1.6A
	250mΩ @ V <sub>GS</sub> = 4.5V	1.3A

## Features and Benefits

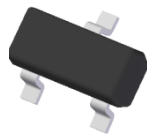
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under separate datasheet ([DMN10H220LQ](#))**

## Description and Applications

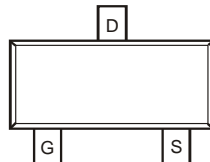
This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Load switches

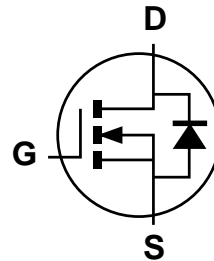
SOT23 (Standard)



Top View



Pin Configuration



Equivalent Circuit

## Ordering Information

Part Number	Package	Packing	
		Qty.	Carrier
DMN10H220L-7	SOT23 (Standard)	3000	Tape & Reel
DMN10H220L-13	SOT23 (Standard)	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



N1H = Marking Code  
 YM = Date Code Marking  
 Y or Y = Year (ex: K = 2023)  
 M = M (ex: 9 = September)

### Date Code Key

Year	2013	...	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	A	...	K	L	M	N	P	R	S	T	U	V

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	100	V
Gate-Source Voltage		V <sub>GSS</sub>	±16	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	(Note 6) T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	1.6 1.3	A
	(Note 5) T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	1.4 1.1	A
Maximum Continuous Body Diode Forward Current (Note 6)		I <sub>S</sub>	0.6	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	8	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.3	W
	T <sub>A</sub> = +70°C		0.8	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	94	°C/W
	(Note 5)		177	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	160	220	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 1.6A
			190	250		
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	401	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	22	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	17	—		
Gate Resistance	R <sub>g</sub>	—	2.1	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	4.1	—	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 1.6A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	8.3	—		
Gate-Source Charge	Q <sub>gs</sub>	—	1.5	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	6.8	—	ns	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 4.5V, R <sub>G</sub> = 6.8Ω, I <sub>D</sub> = 1A
Turn-On Rise Time	t <sub>R</sub>	—	8.2	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	7.9	—		
Turn-Off Fall Time	t <sub>F</sub>	—	3.6	—		
Reverse Recovery Time	t <sub>RR</sub>	—	17	—	ns	I <sub>F</sub> = 1.1A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	9.8	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

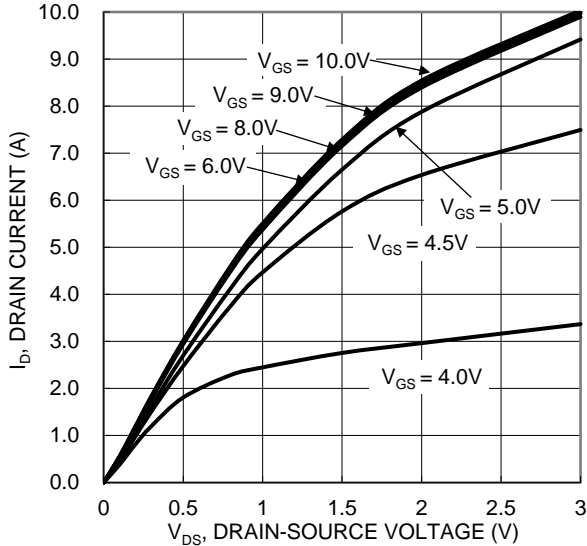


Figure 1. Typical Output Characteristic

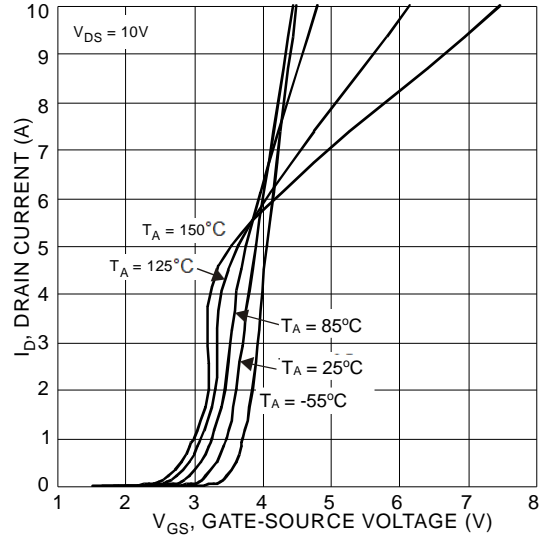


Figure 2 Typical Transfer Characteristics

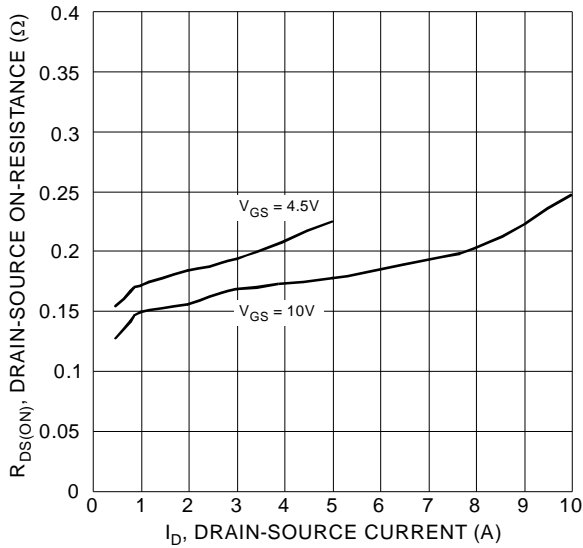


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

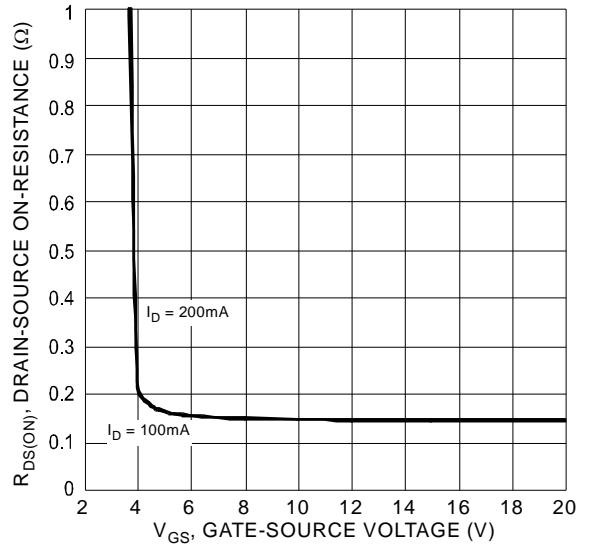


Figure 4 Typical Transfer Characteristic

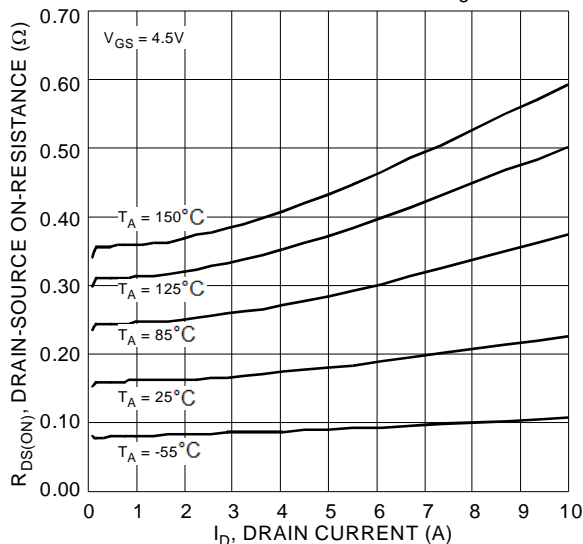


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

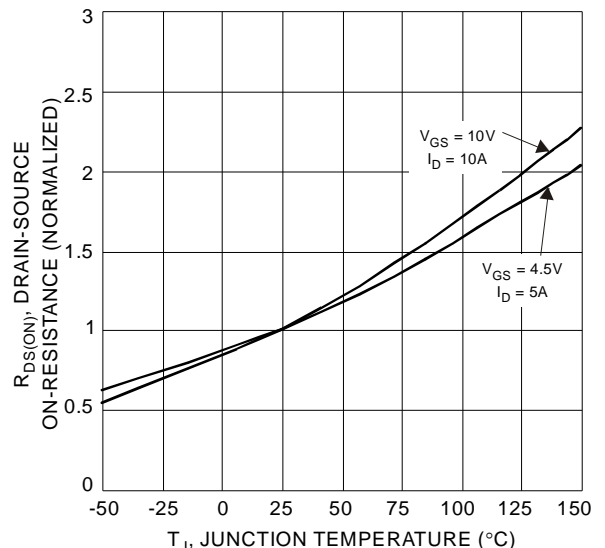


Figure 6 On-Resistance Variation with Temperature

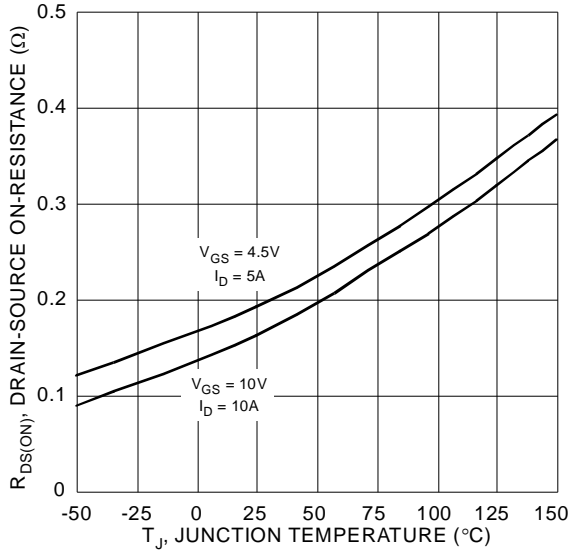


Figure 7 On-Resistance Variation with Temperature

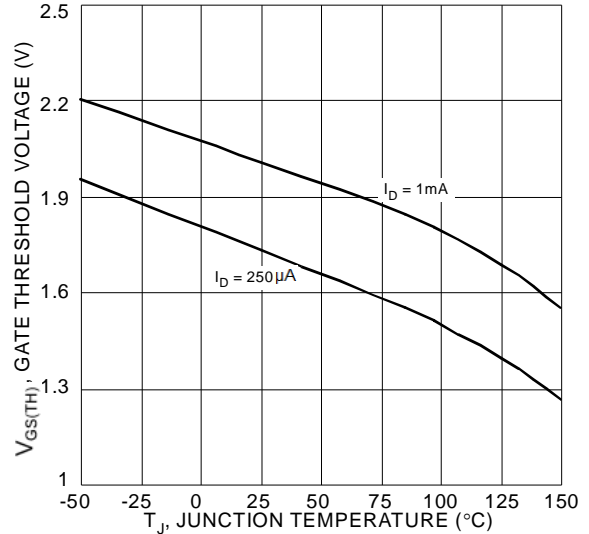


Figure 8 Gate Threshold Variation vs. Ambient Temperature

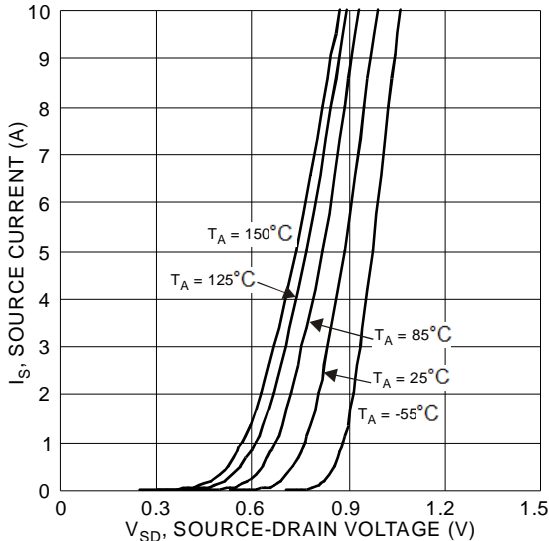


Figure 9 Diode Forward Voltage vs. Current

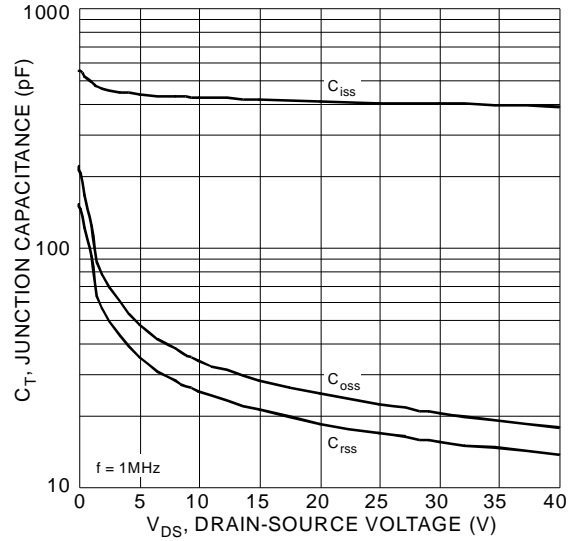


Figure 10 Typical Junction Capacitance

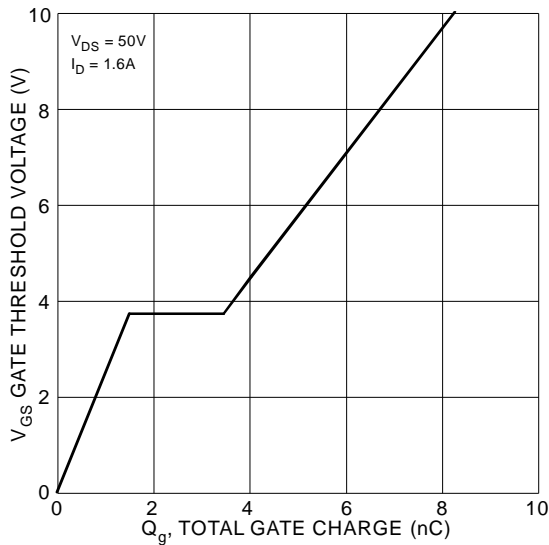


Figure 11 Gate Charge

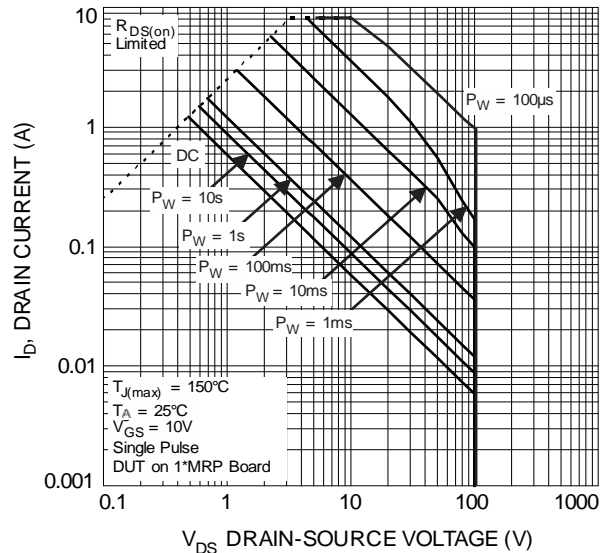
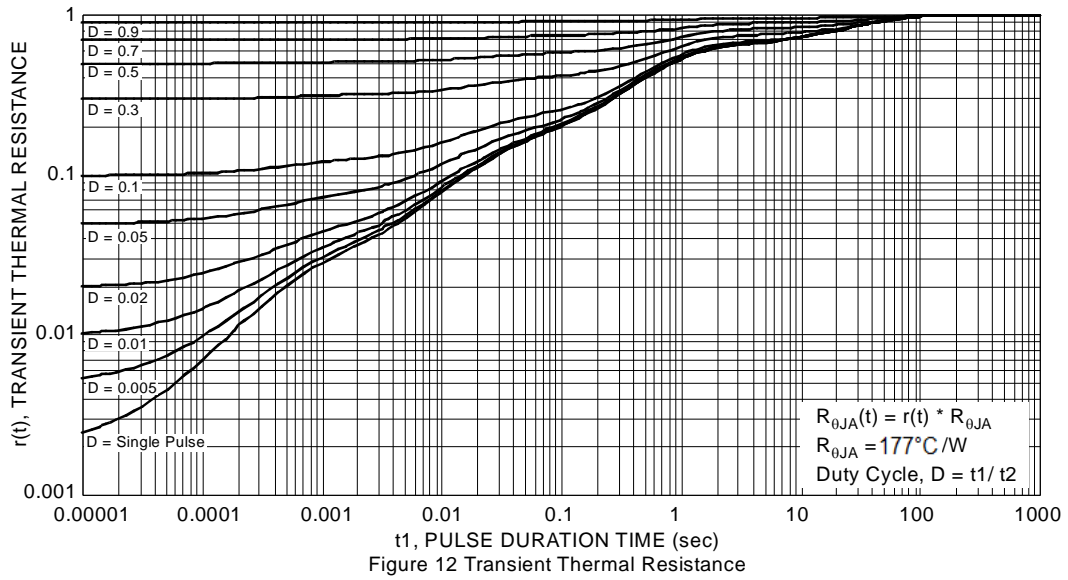


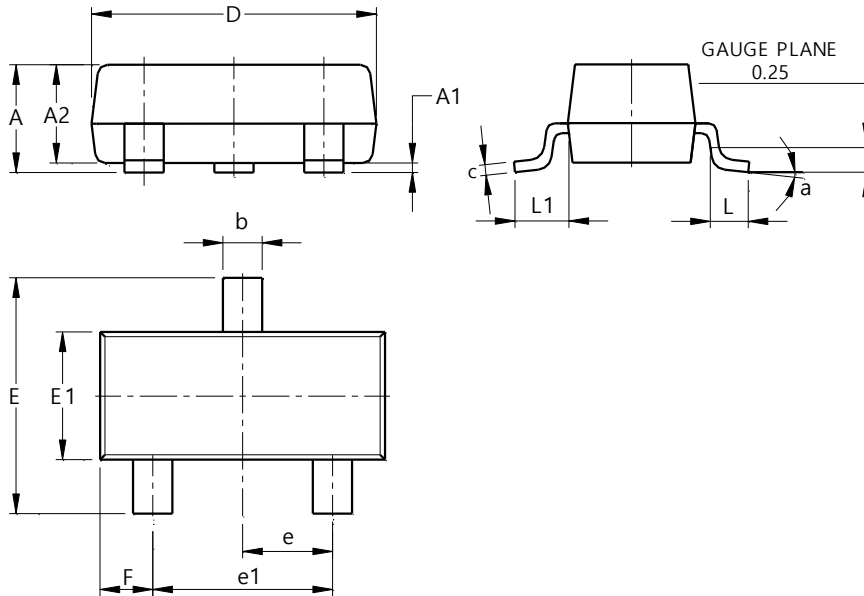
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23 (Standard)**

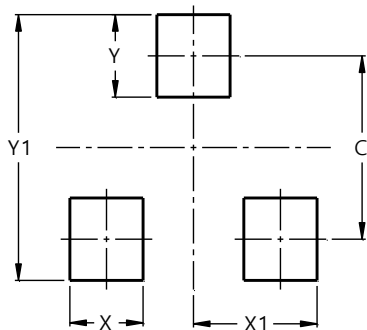


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23 (Standard)**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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